## **Bipolar Junction Transistor (BJT)**

- 1. The arrowhead on the transistor symbol points in the direction of
  - a. electron flow in the emitter region.
  - b. minority carrier flow in the emitter region.
  - c. majority carrier flow in the remitter region.
  - d. Conventional current flow in the emitter region.
- 2. The silicon transistor are more widely used than germanium transistors because
  - a. they have smaller leakage current
  - b. they have better ability to dissipate heat
  - c. they have smaller depletion layer
  - d. they have larger current carrying capacity
- 3. For an NPN transistor in normal bias
  - a. only holes cross the collector junction
  - b. only majority carriers cross the collector junction
  - c. the emitter junction has high resistance
  - d. emitter junction is forward biased and collector junction is reverse biased
- 4. The most commonly used transistor circuit arrangement is
  - a. common base
- b. common emitter
- c. common collector
- d. none of the above
- 5. The emitter of the transistor is doped
  - a. heavily

b. lightly

c. moderately

d. none of these

- 6. For transistor action
  - a. the base region must be very thin and lightly doped.
  - b. the emitter junction must be forward biased and collector junction should be reverse biased.
  - c. the emitter should be heavily doped to supply the required amount of majority carriers.
  - d. all of these.

- 7. The  $I_{CBO}$  is the current that flows when some dc voltage is applied
  - a. in the forward direction to the emitter junction with collector open
  - b. in the reverse direction to the emitter junction with collector open
  - c. in the reverse direction to the collector junction with emitter open
  - d. in the forward direction to the collector junction with emitter open
- 8. The magnitude of current ICBO
  - a. depends largely upon the emitter doping
  - b. depends largely upon emitter-base junction base potential
  - c. Increases with the increase in temperature
  - d. is generally greater in silicon than in germanium transistor
- 9. The current  $I_{CBO}$  flows in the
  - a. emitter and base leads
- b. collector and base leads
- c. emitter and collector leads
- d. none of these
- 10. In CE mode of transistor, the most noticeable effect of a small increase in temperature is
  - a. the increase in output resistance
  - b. the increase in leakage current  $I_{\text{CEO}}$
  - c. the decrease in current gain
  - d. the increase in ac current gain
- 11. In CE configuration, the output V-I characteristics are drawn by taking
  - a.  $V_{CE}$  versus  $I_C$  for constant value of  $I_E$
  - b.  $V_{CE}$  versus  $I_C$  for constant value of  $I_B$
  - c.  $V_{CE}$  versus  $I_E$  for constant value of  $V_{CB}$
  - d. None of these
- 12. In CE configuration, the input V-I characteristics are drawn by taking
  - a.  $V_{CE}$  versus  $I_C$  for constant value of  $I_E$
  - b.  $V_{BE}$  versus  $I_E$  for constant value of  $V_{CE}$
  - c.  $V_{BE}$  versus  $I_B$  for constant value of  $I_C$
  - d.  $V_{BE}$  versus  $I_B$  for constant value of  $V_{CES}$

13. The em	nitter current in	a junction with	normal b	ias				
a.	a. is almost equal to the base current							
b.	b. is equal to the sum of $I_B$ and $I_C$							
	c. changes greatly by a small changes in collector bias voltage							
d.	is equal to I <sub>CBO</sub>							
14 The B	of a transistor m	ay ha datarmir	and direct	v from t	he curve plotted	l hetween		
	14. The $\beta$ of a transistor may be determined direct a. $V_{CE}$ and $I_{C}$ for constant $I_{B}$				b. V <sub>CE</sub> and I <sub>C</sub> for constant I <sub>E</sub>			
C.					$V_{BE}$ and $I_{E}$ for constant $V_{CE}$			
15 In CB c	onfiguration the	outnut V-I ch	aracterist	cs of a ti	ransistor are dra	own hy taking		
	15. In CB configuration, the output V-I characterist a. $V_{CB}$ versus $I_{C}$ for constant $I_{E}$				$V_{CB}$ versus $I_B$ for constant $I_E$			
	c. V <sub>CE</sub> versus I <sub>C</sub> for constant I <sub>E</sub>			b. d.	V <sub>CB</sub> versus I <sub>B</sub> for constant I <sub>E</sub>			
5.	T(E 1919 00 10		5	<b></b>	CB renear is			
16. In which mode of BJT operation are both junction reverse biased								
a.	a. active				saturation			
C.	c. cut off				revers active			
						MM		
17. In which mode of BJT operation are both junction forward biased								
	a. active			b.				
C.	cut off			d.	reverse active			
18 In a hir	oolar junction tra	unsistor the ha	se region i	s made y	very thin so that	-		
<ul><li>18. In a bipolar junction transistor the base region is made very thin so that</li><li>a. recombination in base region is minimum</li></ul>								
b. electric field gradient in base is high								
c.								
d. base can be easily biased								
A								
Answers								
1. (d)	2.	(a)	3.	(d)	4.	(b)		
5. (a)	6.	(d)	7.	(c)	8.	(c)		
9. (b)	10.	(b)	11.	(b)	12.	(d)		
13. (b)	14.	(a)	15.	(b)	16.	(c)		
17. (b)	18.	(a)						